Abstract

Nonvolatile memory element and associated production methods and memory element arrangements

The invention relates to a nonvolatile memory element and to associated production methods and memory element arrangements, in which case, in order to reduce a forming voltage, a first electrode (1) has a field amplifier structure (4) for amplifying a field strength of an electric field (E) generated by means of a second electrode (3) in a changeover material (2).

Figure 3A



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